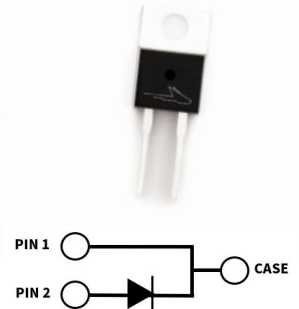


C3D10060A

3rd Generation 600 V, 10 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-220-2
Marking: C3D10060A

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

Maximum Ratings ($T_c = 25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes
Repetitive Peak Reverse Voltage	V_{RRM}	600	V		
DC Blocking Voltage	V_{DC}	600			
Continuous Forward Current	I_F	30	A	$T_J = 25^\circ\text{C}$	Fig. 3
		14.5		$T_J = 135^\circ\text{C}$	
		10		$T_J = 152^\circ\text{C}$	
Repetitive Peak Forward Surge Current	I_{FRM}	46		$T_c = 25^\circ\text{C}, t_p = 10 \text{ ms}$, Half Sine Wave	Fig. 8
		31		$T_c = 110^\circ\text{C}, t_p = 10 \text{ ms}$, Half Sine Wave	
Non-Repetitive Forward Surge Current	I_{FSM}	90		$T_c = 25^\circ\text{C}, t_p = 10 \text{ ms}$, Half Sine Wave	
		71		$T_c = 110^\circ\text{C}, t_p = 10 \text{ ms}$, Half Sine Wave	
Non-Repetitive Peak Forward Surge Current	$I_{F,Max}$	860		$T_c = 25^\circ\text{C}, t_p = 10 \mu\text{s}$, Pulse	
		680		$T_c = 110^\circ\text{C}, t_p = 10 \mu\text{s}$, Pulse	
Power Dissipation	P_{tot}	136.5	W	$T_J = 25^\circ\text{C}$	Fig. 4
		59		$T_J = 110^\circ\text{C}$	

Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Notes
Forward Voltage	V _F	1.5	1.8	V	I _F = 10 A, T _j = 25 °C	Fig. 1
		2.0	2.4		I _F = 10 A, T _j = 175 °C	
Reverse Current	I _R	10	50	μA	V _R = 600 V, T _j = 25 °C	Fig. 2
		20	200		V _R = 600 V, T _j = 175 °C	
Total Capacitive Charge	Q _C	24		nC	V _R = 400 V, T _j = 25 °C	Fig. 5
Total Capacitance	C	460.5		pF	V _R = 0 V, T _j = 25 °C, f = 1 MHz	Fig. 6
		44			V _R = 200 V, T _j = 25 °C, f = 1 MHz	
		40			V _R = 400 V, T _j = 25 °C, f = 1 MHz	
Capacitance Stored Energy	E _c	3.6		μJ	V _R = 400 V	Fig. 7

Notes:
SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R _{θ, JC (TYP)}	1.1	°C / W	
Junction Temperature	T _j	-55 to +175	°C	
Case & Storage Temperature	T _c	-55 to +175		
TO-220 Mounting Torque	-	1	Nm	M3 Screw
		8.8	lbf-in	6-32 Screw

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Notes
Human Body Model	HBM	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Typical Performance

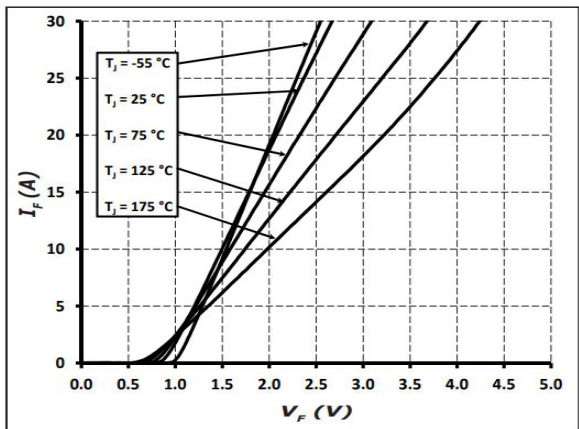


Figure 1
Forward Characteristics

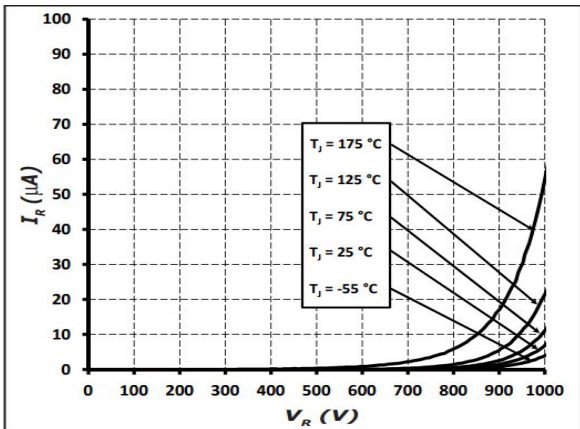


Figure 2
Reverse Characteristics

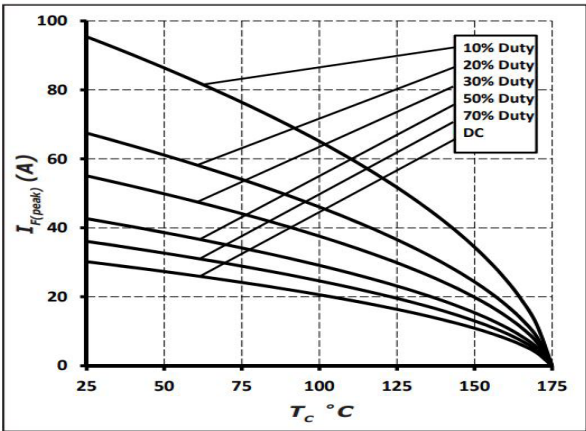


Figure 3
Current Derating

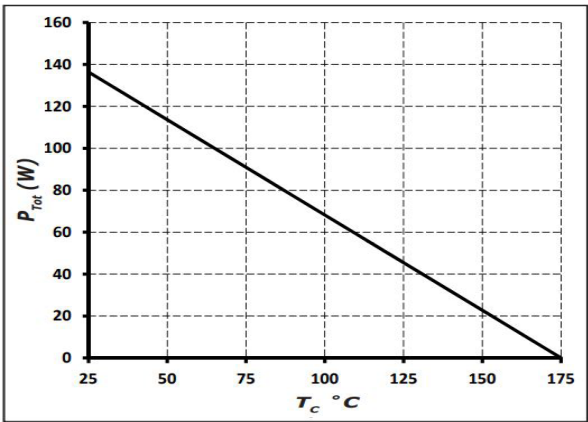


Figure 4
Power Derating

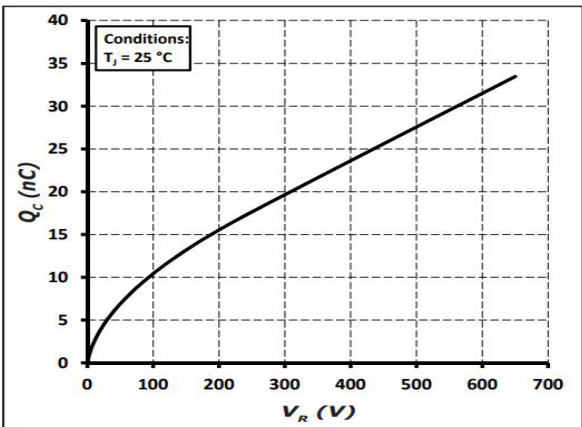


Figure 5
Total Capacitance Charge vs. Reverse Voltage

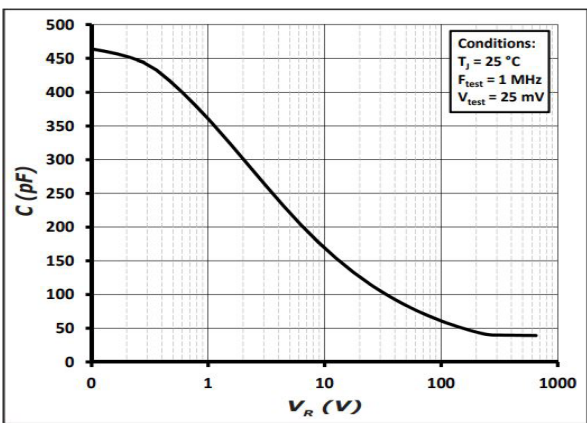


Figure 6
Capacitance vs. Reverse Voltage

Typical Performance

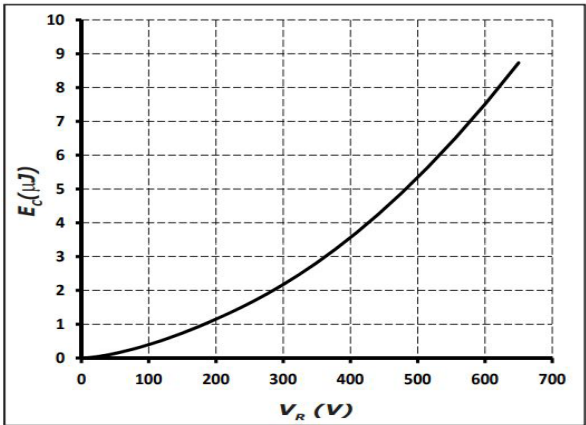


Figure 7
Capacitance Stored Energy

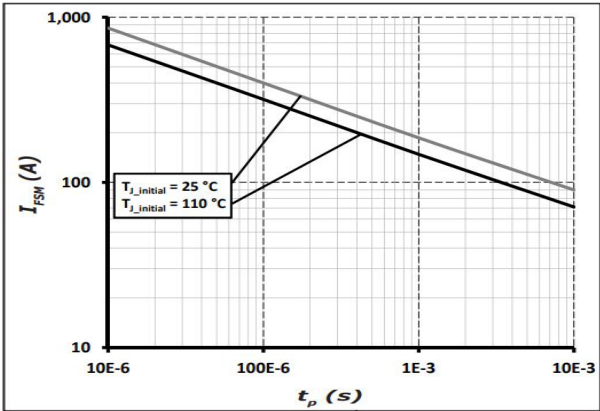


Figure 8
Non-Repetitive Peak Forward Surge Current vs. Pulse Duraion

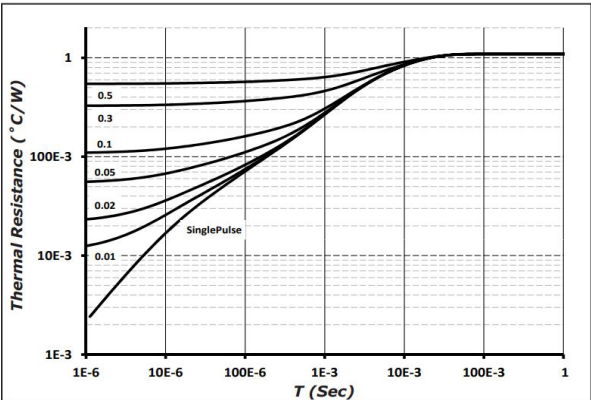
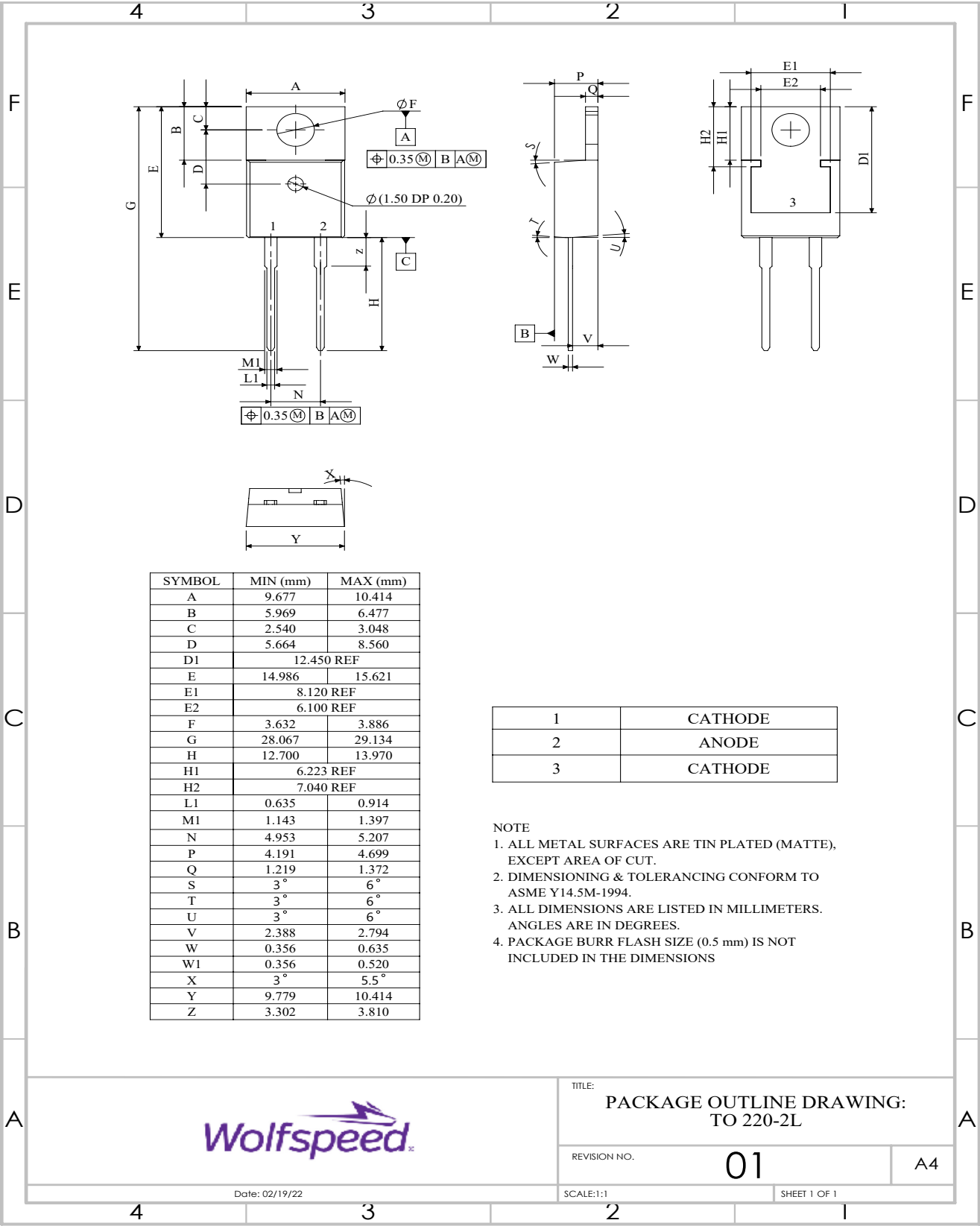


Figure 9
Transient Thermal Impedance

Package Dimensions & Pin-Out

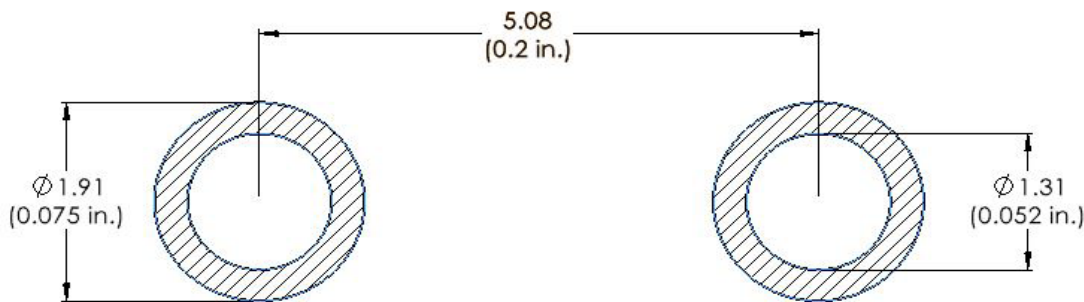
Package: TO-220-2





Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type
C3D10060A	Tube



Revision History

Document Version	Date of Release	Description of Changes
1	August-2016	Initial Release
8	March-2023	Update Package Drawing Update Landing Pad

Notes & Disclaimer

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